

MOSFET

OptiMOS™ Power Transistor, -60 V

Features

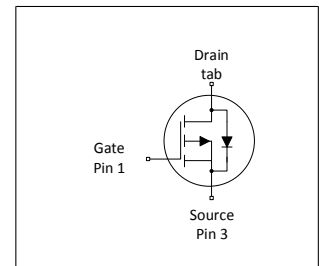
- P-Channel
- Very low on-resistance $R_{DS(on)}$
- 100% avalanche tested
- Normal Level
- Enhancement mode
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on),max}$	400	m Ω
I_D	-4.3	A



Type / Ordering Code	Package	Marking	Related Links
IPD40DP06NM	PG-TO 252-3	40DP06NM	-

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1 Maximum ratings

at $T_C=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	-4.3 -3.3	A	$V_{GS}=-10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=-10\text{ V}$, $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	-17.2	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	43	mJ	$I_D=-4.3\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	19	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	7.9	°C/W	-
Device on PCB, 6 cm ² cooling area ³⁾	R_{thJA}	-	-	75	°C/W	-

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=-250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-2.1	-3	-4	V	$V_{DS}=V_{GS}$, $I_D=-166\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-0.1 -10	-1 -100	μA	$V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	$V_{GS}=-20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	328	400	m Ω	$V_{GS}=-10\text{ V}$, $I_D=-4.3\text{ A}$
Gate resistance	R_G	-	4	-	Ω	-
Transconductance	g_{fs}	-	3.8	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=-4.3\text{ A}$

¹⁾ See Diagram 3 for more detailed information

²⁾ See Diagram 13 for more detailed information

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	260	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	40	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	12	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	4	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-2.15\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Rise time	t_r	-	6	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-2.15\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	10	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-2.15\text{ A}$, $R_{G,ext}=1.6\ \Omega$
Fall time	t_f	-	4	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-2.15\text{ A}$, $R_{G,ext}=1.6\ \Omega$

Table 6 Gate charge characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.5	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	0.8	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate to drain charge	Q_{gd}	-	2.7	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Switching charge	Q_{sw}	-	3.4	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge total	Q_g	-	6.7	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.7	-	V	$V_{DD}=-30\text{ V}$, $I_D=-4.3\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Output charge	Q_{oss}	-	-2.9	-	nC	$V_{DD}=-30\text{ V}$, $V_{GS}=0\text{ V}$

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-4.3	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	-17.2	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	-0.9	-1.2	V	$V_{GS}=0\text{ V}$, $I_F=-4.3\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	36	-	ns	$V_R=-30\text{ V}$, $I_F=-4.3\text{ A}$, $di_F/dt=-100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	-60	-	nC	$V_R=-30\text{ V}$, $I_F=-4.3\text{ A}$, $di_F/dt=-100\text{ A}/\mu\text{s}$

¹⁾ See diagram ,Gate charge waveforms, for gate charge parameter definition

4 Electrical characteristics diagrams

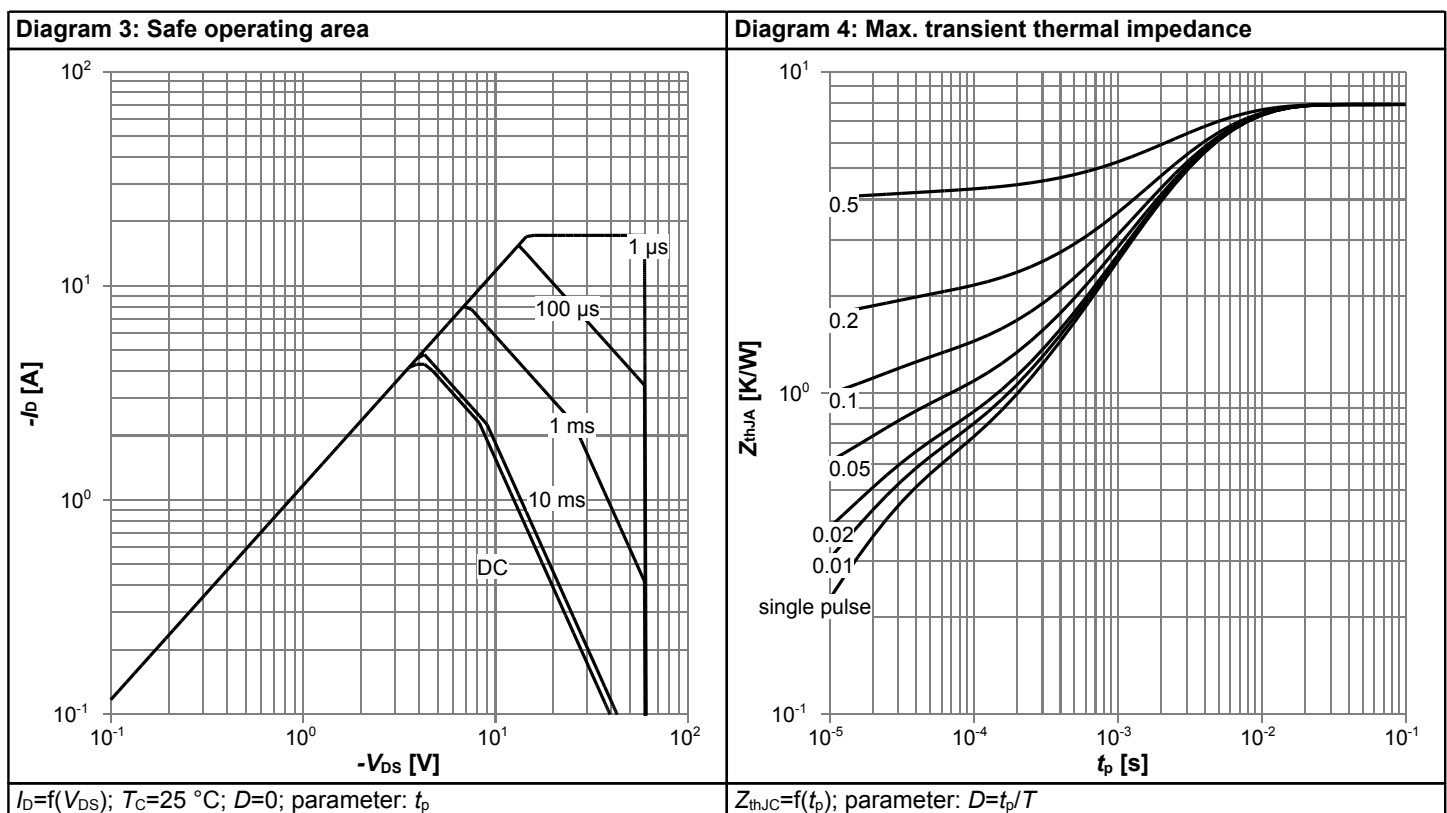
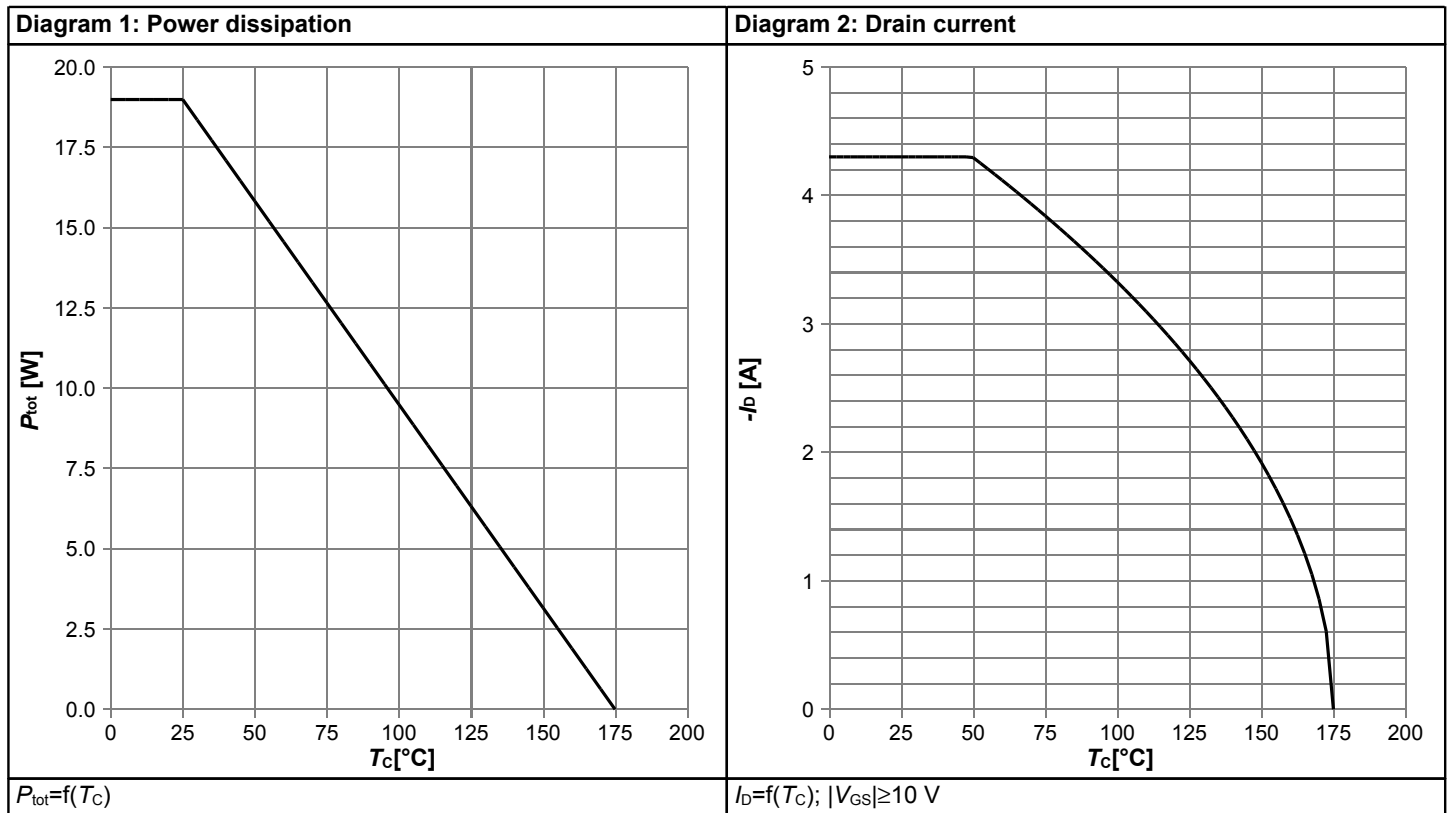
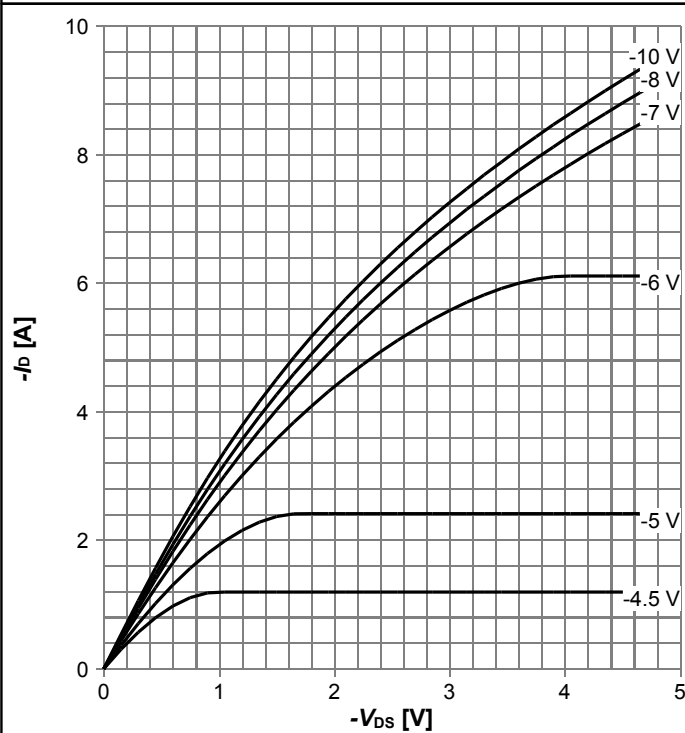
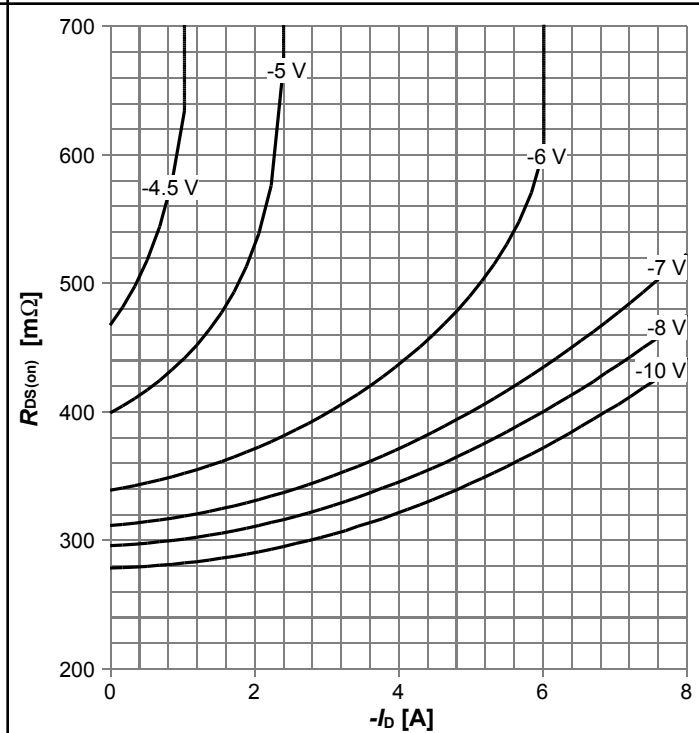


Diagram 5: Typ. output characteristics



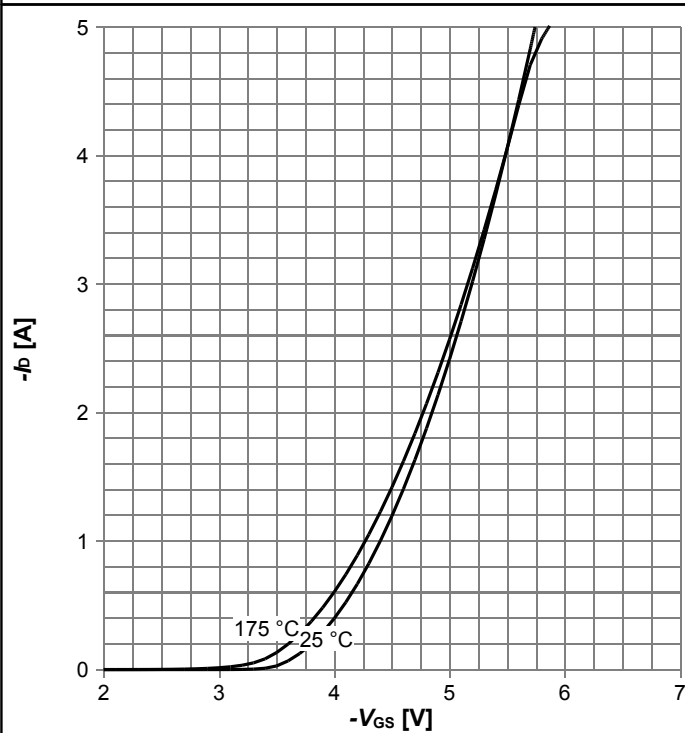
$I_D = f(V_{DS})$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



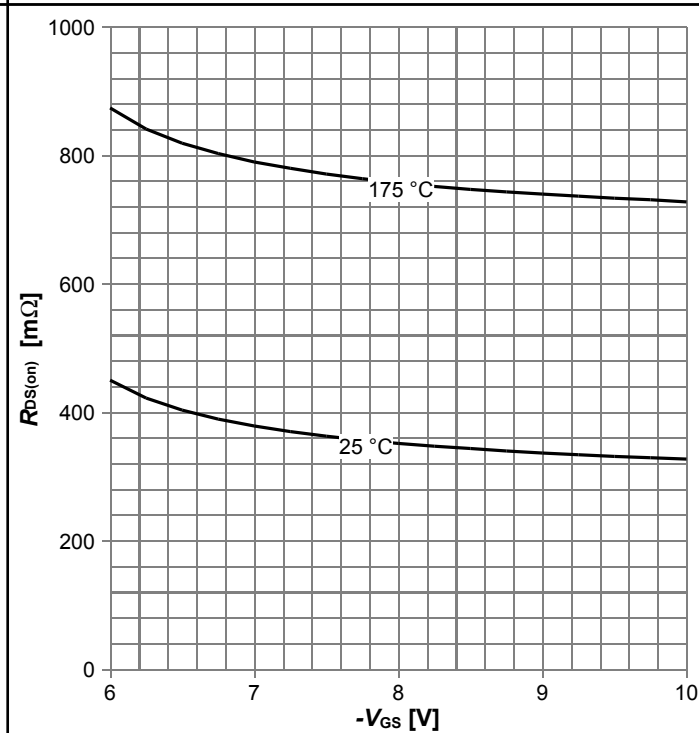
$R_{DS(on)} = f(I_D)$, $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



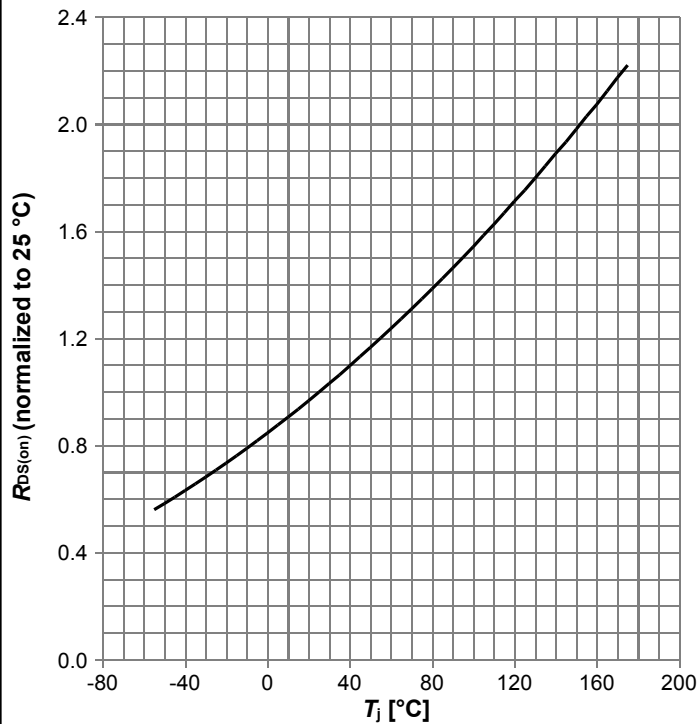
$I_D = f(V_{GS})$, $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



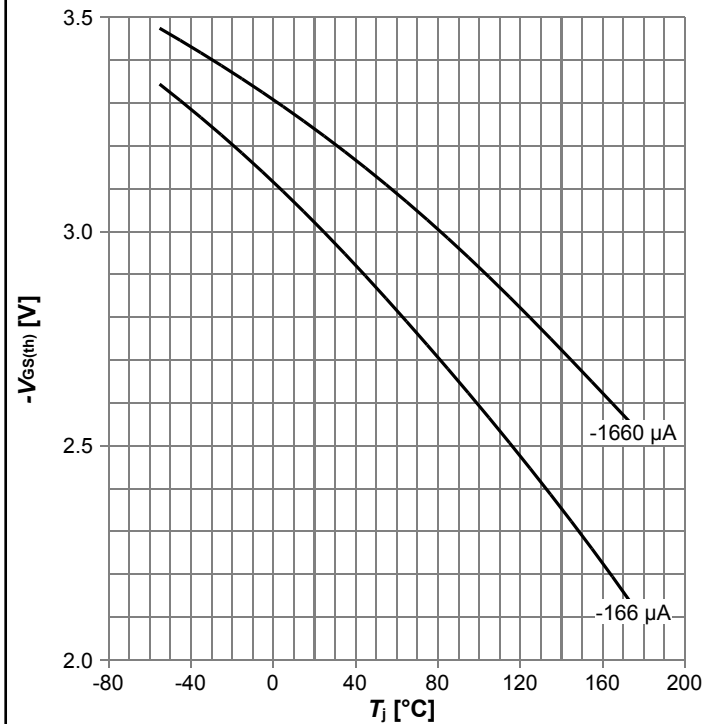
$R_{DS(on)} = f(V_{GS})$, $I_D = -4.3\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



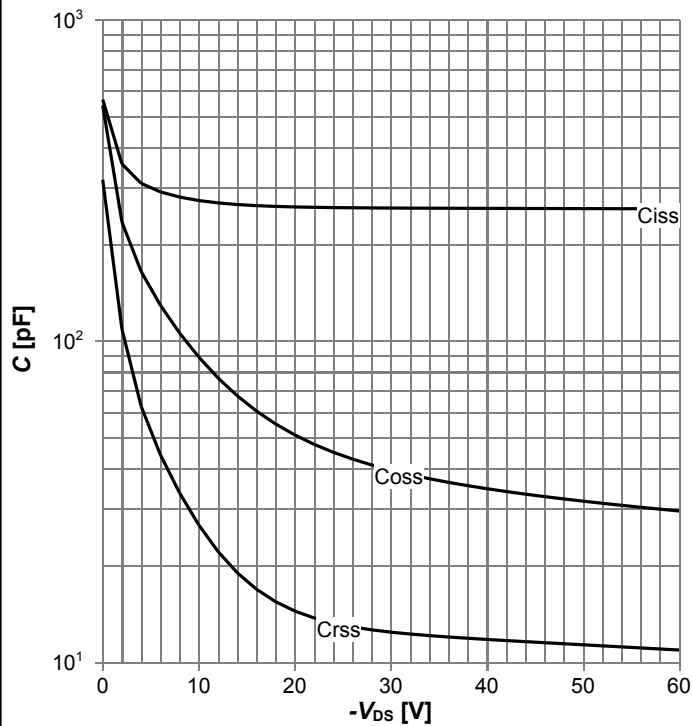
$$R_{DS(on)} = f(T_j), I_D = 4.3 \text{ A}, V_{GS} = -10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



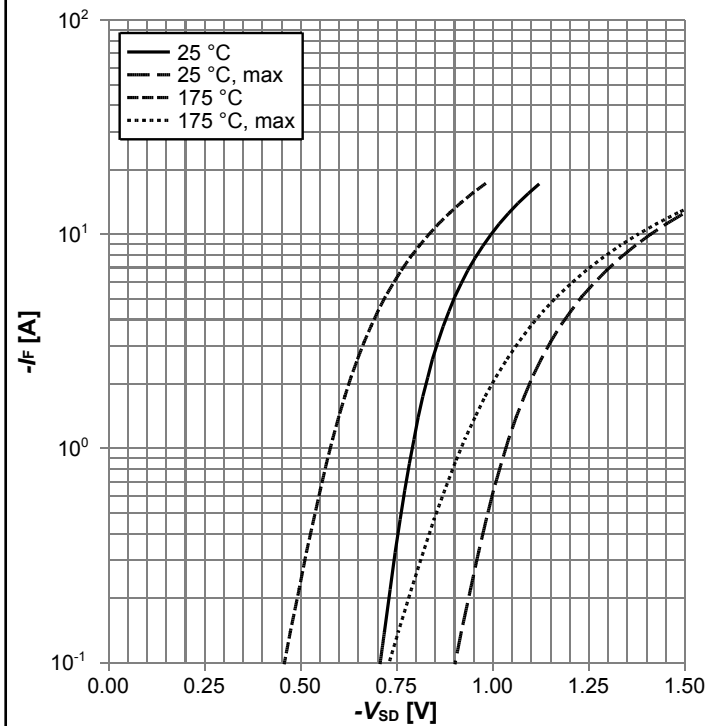
$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 11: Typ. capacitances



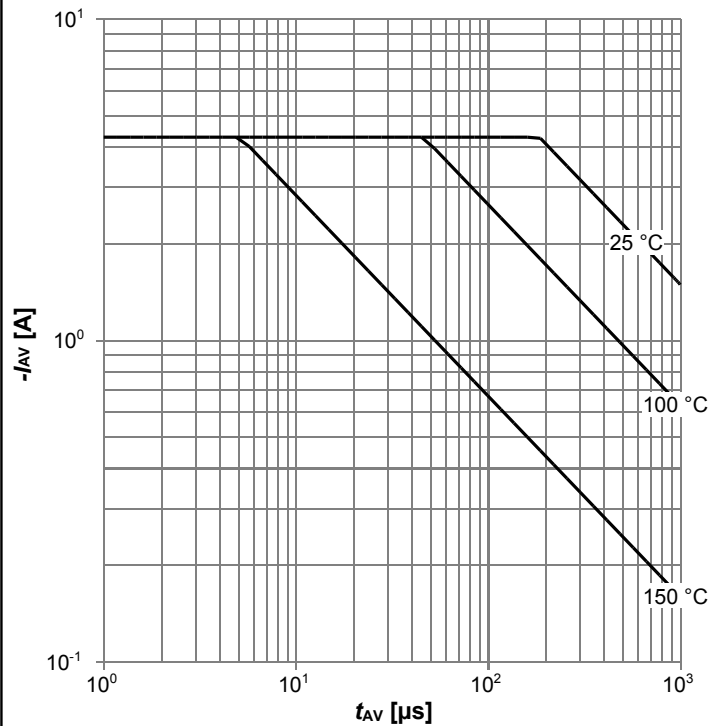
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



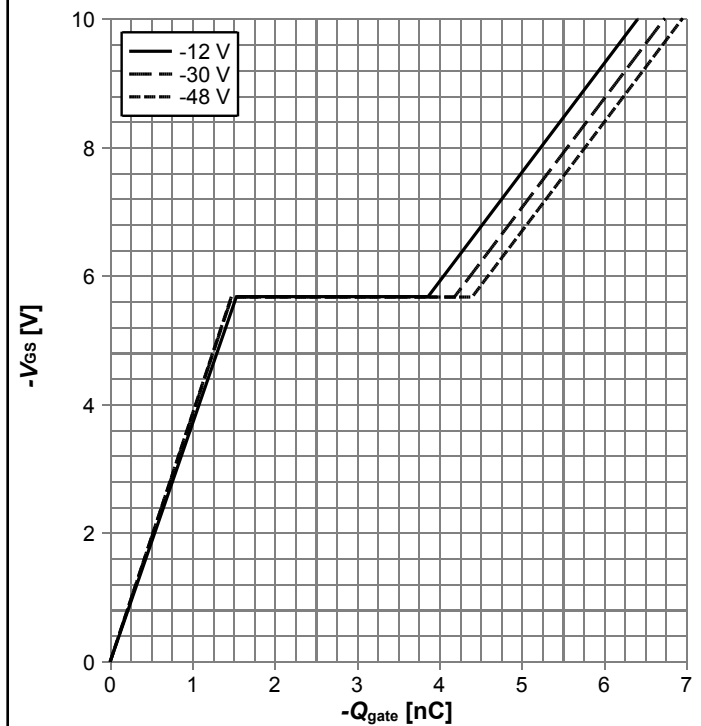
$$I_F = f(V_{SD}); \text{ parameter: } T_j$$

Diagram 13: Avalanche characteristics



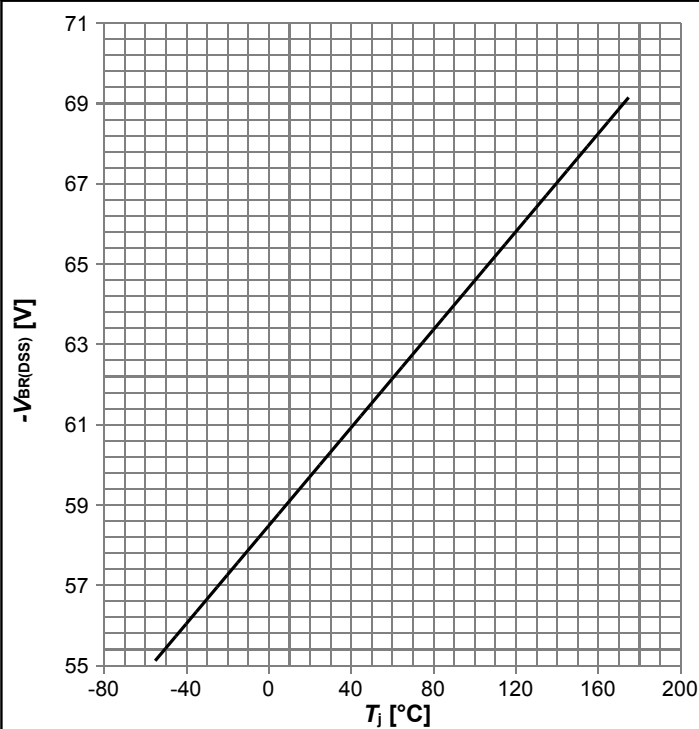
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



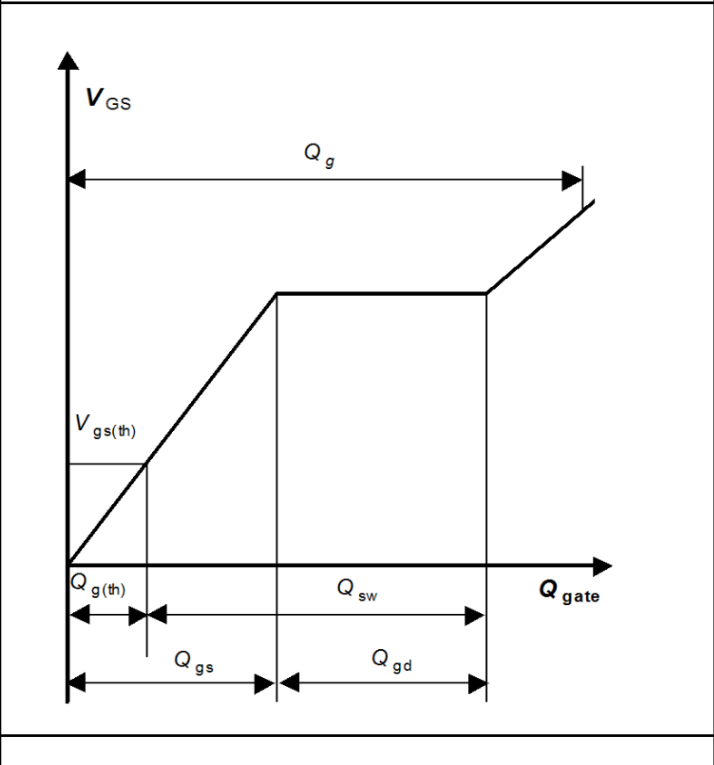
$V_{GS}=f(Q_{gate})$, $I_D=-4.3\text{ A}$ pulsed, $T_j=25\text{ °C}$; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

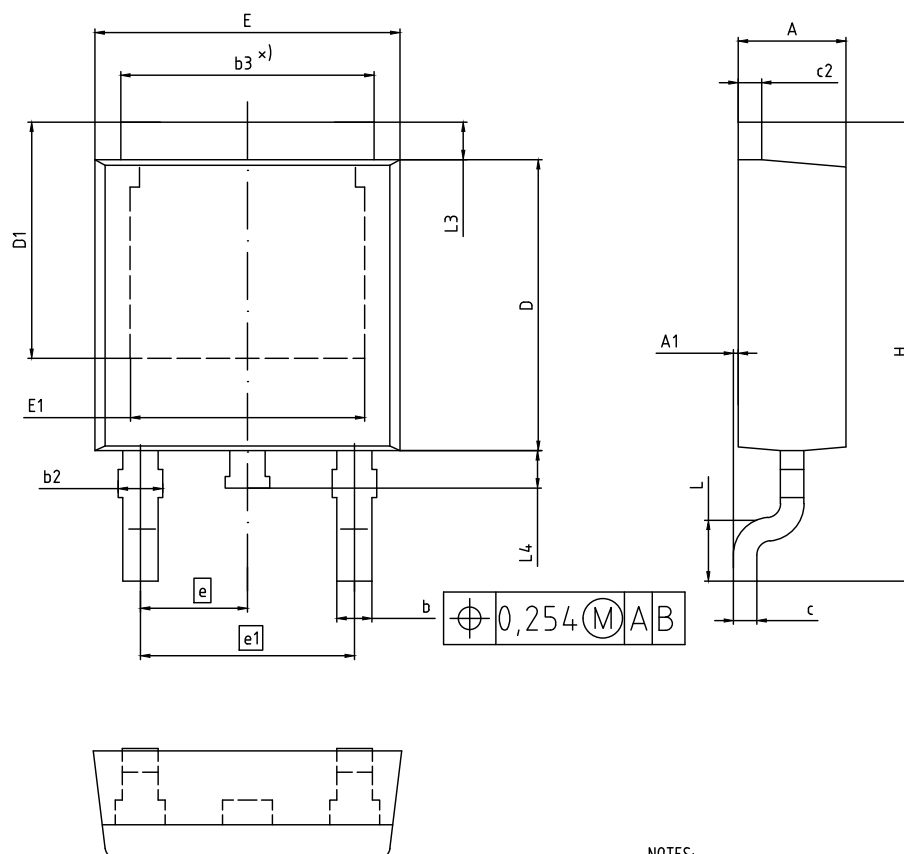


$V_{BR(DSS)}=f(T_j)$; $I_D=-250\ \mu\text{A}$

Diagram Gate charge waveforms



5 Package Outlines



NOTES:

1. INDUSTRIAL QUALITY GRADE
2. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DOCUMENT NO. Z8B00003328
SCALE 0 2.5 5mm
EUROPEAN PROJECTION
ISSUE DATE 05-02-2016
REVISION 06

Figure 1 Outline PG-TO 252-3, dimensions in mm/inches

Revision History

IPD40DP06NM

Revision: 2019-03-26, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-03-26	Release of final version

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